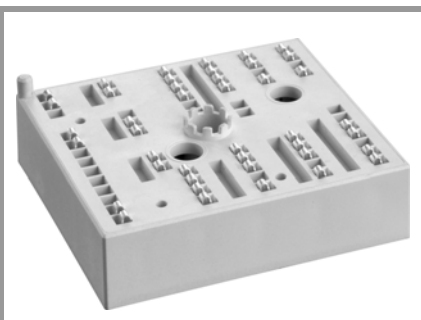


# SKiIP25AC12T4V25



MiniSKiIP® 2

## SKiIP25AC12T4V25

### Features

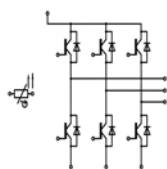
- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

### Typical Applications\*

- Inverter up to 26 kVA
- Typical motor power 15 kW

### Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ )
- Dynamic test results for  $V_{CC} = 600\text{V}$ ,  $R_{Gon/off} = 12\Omega$ ,  $I_C = 50\text{A}$ ,  $V_{GE} = \pm 15\text{V}$ :  $E_{on} = 5.6\text{mJ}$ ,  $E_{off} = 6.1\text{mJ}$ ,  $E_{rr} = 3.3\text{mJ}$ ,  $di/dt_{on} = 1440\text{A}/\mu\text{s}$ ,  $t_{don} = 58\text{ns}$ ,  $t_r = 43\text{ns}$ ,  $di/dt_{off} = 600\text{A}/\mu\text{s}$ ,  $t_{doff} = 370\text{ns}$ ,  $t_f = 65\text{ns}$



AC

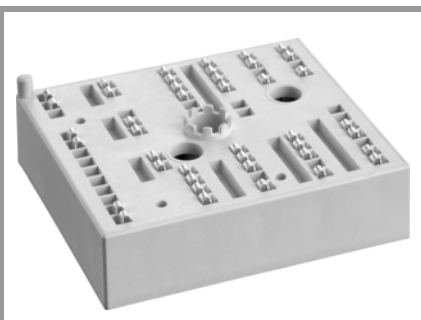
### Absolute Maximum Ratings

Symbol	Conditions	Values	Unit	
<b>Inverter - IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200	V	
$I_C$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	69	A
		$T_s = 70^\circ\text{C}$	56	A
$I_{Cnom}$		50	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	150	A	
$V_{GES}$		-20 ... 20	V	
$t_{psc}$	$V_{CC} = 800\text{V}$	$T_j = 150^\circ\text{C}$	10	$\mu\text{s}$
	$V_{GE} \leq 15\text{V}$ $V_{CES} \leq 1200\text{V}$			
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Inverse - Diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	60	A
		$T_s = 70^\circ\text{C}$	48	A
$I_{Fnom}$		50	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	150	A	
$I_{FSM}$	10 ms, sin 180°, $T_j = 150^\circ\text{C}$	270	A	
$T_j$		-40 ... 175	$^\circ\text{C}$	
<b>Module</b>				
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}$ , 20A per spring	60	A	
$T_{stg}$		-40 ... 125	$^\circ\text{C}$	
$V_{isol}$	AC sinus 50Hz, t = 1 min	2500	V	

### Characteristics

Symbol	Conditions	min.	typ.	max.	Unit
<b>Inverter - IGBT</b>					
$V_{CE(sat)}$	$I_C = 50\text{A}$ $V_{GE} = 15\text{V}$ chipelevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.20	2.40	V
$V_{CE0}$		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
$r_{CE}$	$V_{GE} = 15\text{V}$	$T_j = 25^\circ\text{C}$	21	24	m $\Omega$
		$T_j = 150^\circ\text{C}$	30	32	m $\Omega$
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 1.7\text{mA}$	5	5.8	6.5	V
$I_{CES}$	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
$C_{ies}$	$V_{CE} = 25\text{V}$		2.77		nF
$C_{oes}$	$V_{GE} = 0\text{V}$		0.20		nF
$C_{res}$			0.16		nF
$Q_G$	- 8 V...+ 15 V		283		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$		4		$\Omega$
$t_{d(on)}$	$V_{CC} = 800\text{V}$	$T_j = 150^\circ\text{C}$	45		ns
$t_r$	$I_C = 22\text{A}$	$T_j = 150^\circ\text{C}$	19		ns
$E_{on}$	$R_{Gon} = 12\Omega$	$T_j = 150^\circ\text{C}$	3.4		mJ
$t_{d(off)}$	$R_{Goff} = 1\Omega$ $di/dt_{on} = 1640\text{A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	480		ns
$t_f$	$di/dt_{off} = 320\text{A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$	44		ns
$E_{off}$	$V_{GE} = +15/0\text{V}$	$T_j = 150^\circ\text{C}$	3.1		mJ
$R_{th(j-s)}$	per IGBT		0.71		K/W

# SKiiP25AC12T4V25



MiniSKiiP® 2

## SKiiP25AC12T4V25

### Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

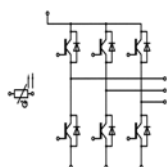
### Typical Applications\*

- Inverter up to 26 kVA
- Typical motor power 15 kW

### Remarks

- $V_{CEsat}$ ,  $V_F$  = chip level value
- Case temp. limited to  $T_C = 125^\circ\text{C}$  max. (for baseplateless modules  $T_C = T_S$ )
- product rel. results valid for  $T_j \leq 150$  (recomm.  $T_{op} = -40 \dots +150^\circ\text{C}$ )
- Dynamic test results for  $V_{cc} = 600\text{V}$ ,  $R_{Gon/off} = 12\Omega$ ,  $I_C = 50\text{A}$ ,  $V_{GE} = \pm 15\text{V}$ :  $E_{on} = 5.6\text{mJ}$ ,  $E_{off} = 6.1\text{mJ}$ ,  $E_{rr} = 3.3\text{mJ}$ ,  $di/dt_{on} = 1440\text{A}/\mu\text{s}$ ,  $t_{don} = 58\text{ns}$ ,  $t_r = 43\text{ns}$ ,  $di/dt_{off} = 600\text{A}/\mu\text{s}$ ,  $t_{doff} = 370\text{ns}$ ,  $t_f = 65\text{ns}$

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
<b>Inverse - Diode</b>						
$V_F = V_{EC}$	$I_F = 50\text{ A}$ $V_{GE} = 0\text{ V}$ chiplevel	$T_j = 25^\circ\text{C}$		2.2	2.5	V
		$T_j = 150^\circ\text{C}$		2.2	2.5	V
$V_{F0}$		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
$r_F$		$T_j = 25^\circ\text{C}$		18	21	m $\Omega$
		$T_j = 150^\circ\text{C}$		26	28	m $\Omega$
$I_{RRM}$	$I_F = 22\text{ A}$	$T_j = 150^\circ\text{C}$		0		A
$Q_{rr}$	$di/dt_{off} = 1680\text{ A}/\mu\text{s}$ $V_{GE} = 0\text{ V}$	$T_j = 150^\circ\text{C}$		5.5		$\mu\text{C}$
$E_{rr}$	$V_{CC} = 800\text{ V}$	$T_j = 150^\circ\text{C}$		2.9		mJ
$R_{th(j-s)}$	per Diode			0.95		K/W
<b>Module</b>						
$M_s$	to heat sink		2		2.5	Nm
w				65		g
<b>Temperatur Sensor</b>						
$R_{100}$	$T_C = 100^\circ\text{C}$ ( $R_{25} = 1000\Omega$ )			1670 $\pm$ 3%		$\Omega$
$R(T)$	$R(T) = 1000\Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$ ], $A = 7.635 \cdot 10^{-3} \text{ }^\circ\text{C}^{-1}$ , $B = 1.731 \cdot 10^{-5} \text{ }^\circ\text{C}^{-2}$					



AC

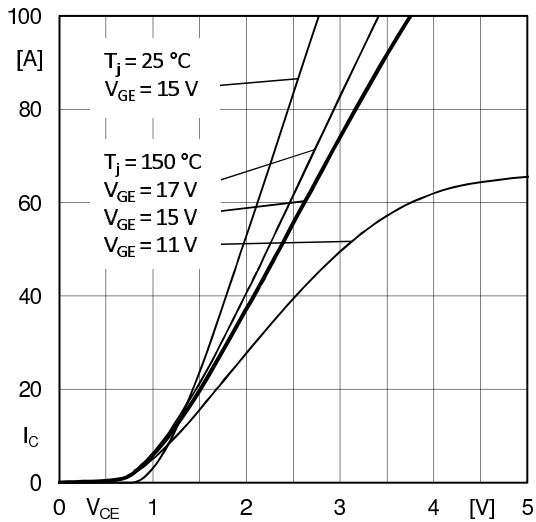


Fig. 1: Typ. output characteristic, inclusive  $R_{CC'+EE'}$

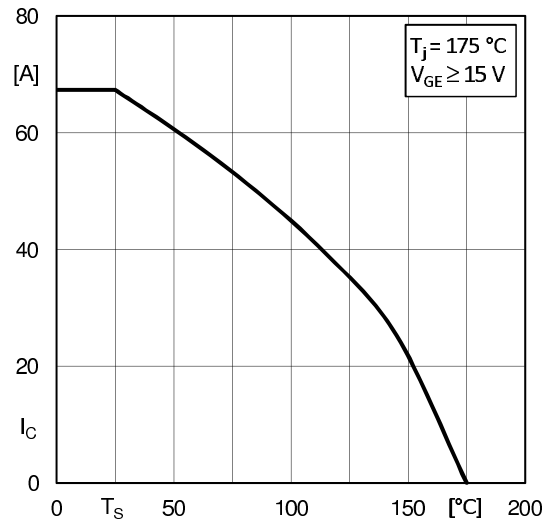


Fig. 2: Rated current vs. temperature  $I_c = f(T_s)$

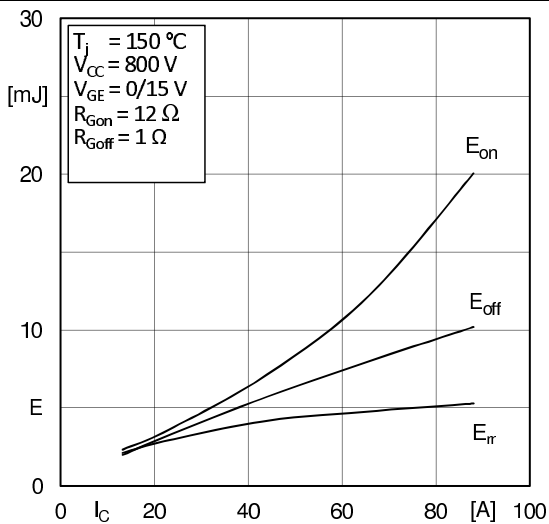


Fig. 3: Typ. turn-on /-off energy =  $f(I_c)$

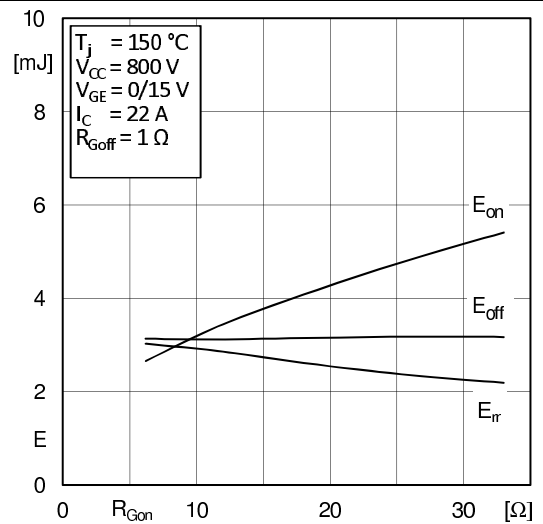


Fig. 4: Typ. turn-on /-off energy =  $f(R_G)$

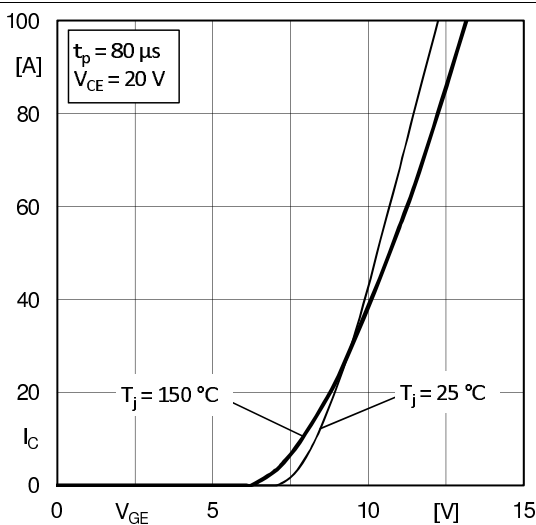


Fig. 5: Typ. transfer characteristic

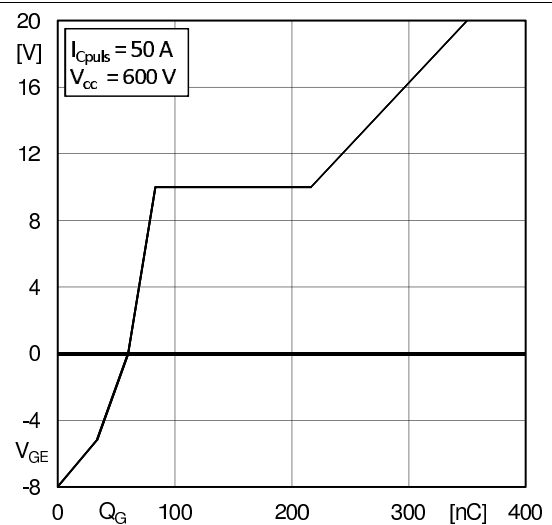


Fig. 6: Typ. gate charge characteristic

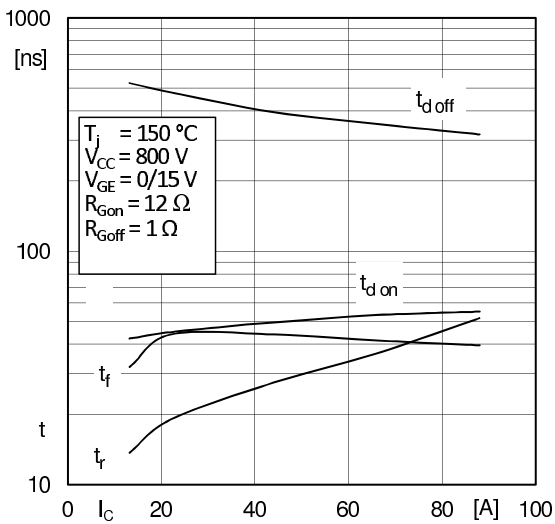


Fig. 7: Typ. switching times vs.  $I_C$

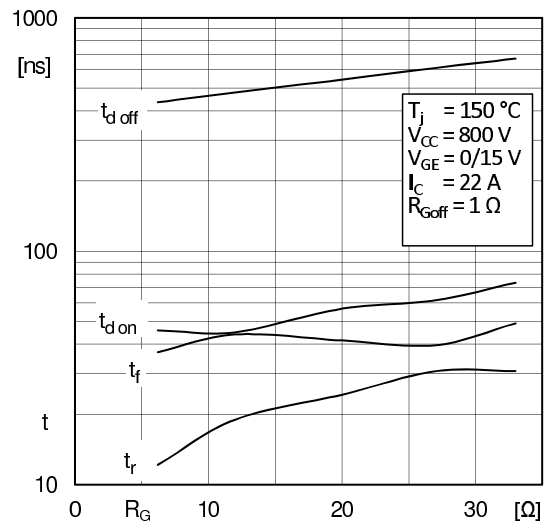


Fig. 8: Typ. switching times vs. gate resistor  $R_G$

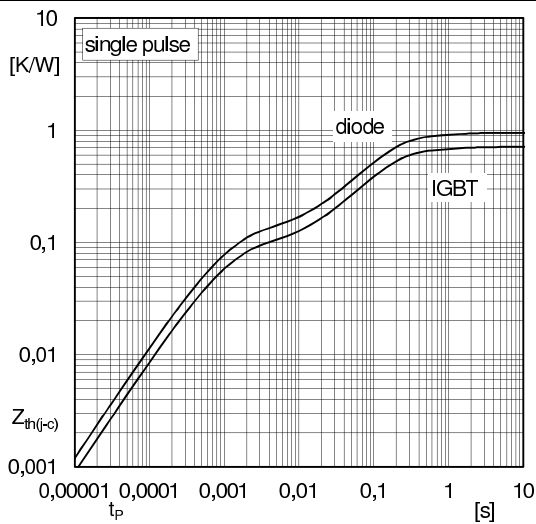


Fig. 9: Transient thermal impedance of IGBT and Diode

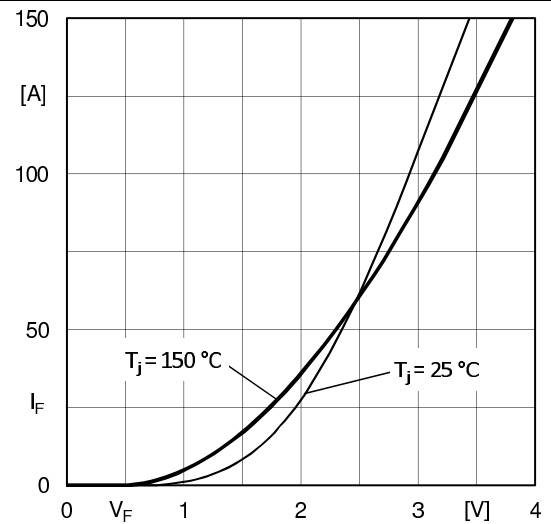
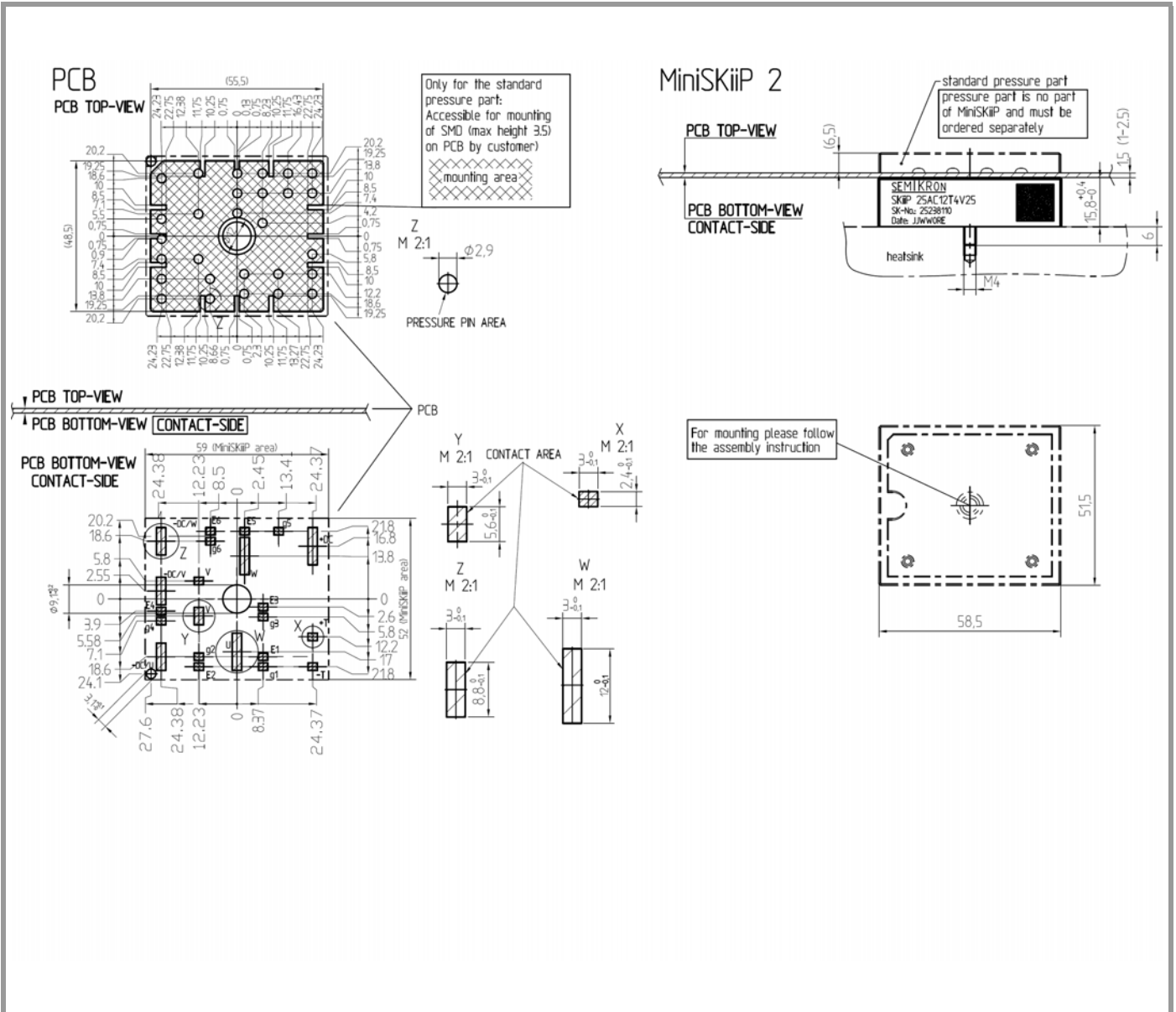


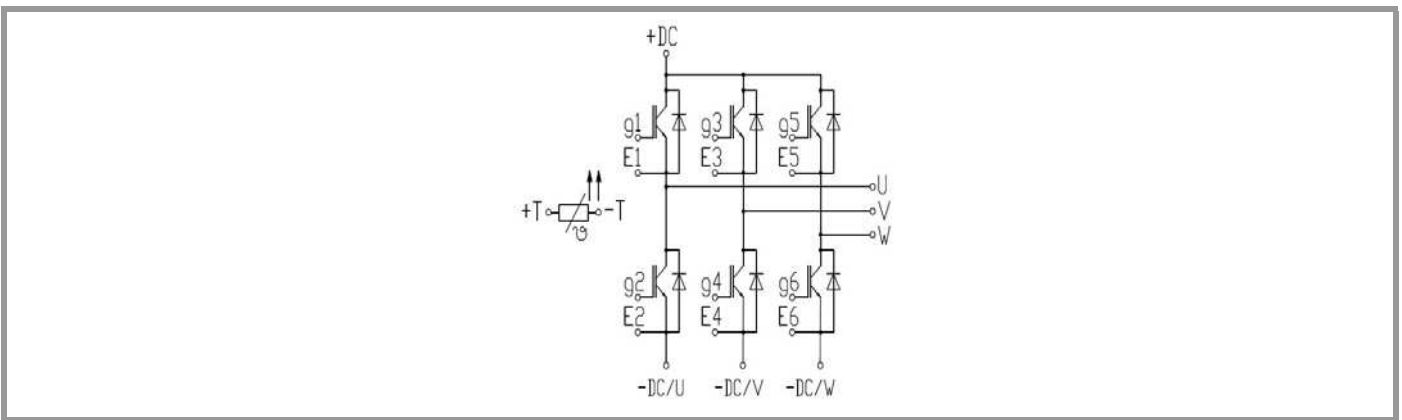
Fig. 10: CAL diode forward characteristic

Fig. 11: Typ. CAL diode peak reverse recovery current

Fig. 12: Typ. CAL diode recovery charge



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.

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